

60V PNP LOW SATURATION MEDIUM POWER TRANSISTOR

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

Features

- BV_{CEO} > -60V
- R_{SAT} = 53mΩ Typical
- Continuous Collector Current I_C = -6A
- Up to -15A Peak Current
- Low Equivalent On Resistance
- Low Saturation Voltage
- High Gain Holds Up (100 Min @ -2A)
- Lead-Free Finish; RoHS compliant (Note 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Application

- DC-DC Converters
- Power Switches
- Motor Control
- Automotive Circuits
- Inverter Circuits

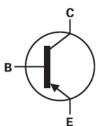
Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.34 grams (Approximate)

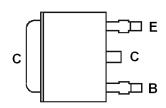




Top View



Device Schematic



Pin Out Configuration Top view

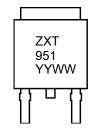
Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXT951KQTC	Automotive	ZXT951	13	16	2,500

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZXT951 = Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 16 = 2016) WW = Week Code (01 ~ 53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	BV _{CBO}	-100	V
Collector-Base Voltage	BV _{CER}	-100	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-6	Α
Base Current	I _B	-0.5	A
Peak Pulse Collector Current	I _{CM}	-15	А

Thermal Characteristics (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Note 6)		2.1		
Power Dissipation	(Note 7)	P_{D}	3.2	W	
	(Note 8)		4.2		
	(Note 6)		59		
Thermal Resistance, Junction to Ambient Air	(Note 7)	$R_{ hetaJA}$	39	°C/W	
	(Note 8)		30		
Thermal Resistance, Junction to Leads (Note 9)		$R_{ heta JL}$	1.77	°C/W	
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C	

ESD Ratings (Note 10)

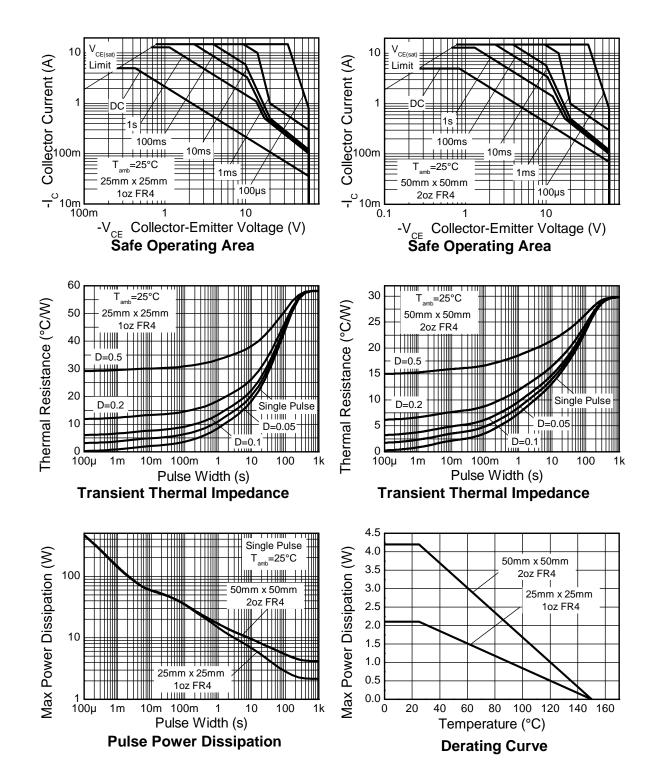
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	8,000	V	3B
Electrostatic Discharge – Machine Model	ESD MM	400	V	С

Notes:

- $6. \ For the device mounted on 25 mm\ x\ 25 mm\ x\ 1.6 mm\ FR4\ PCB\ with\ high\ coverage\ of\ single\ sided\ 1oz\ copper,\ in\ still\ air\ conditions.$
- For the device mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
 For the device mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
 For the device mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.
 Thermal resistance from junction to solder-point (at the end of the collector lead).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Typical Thermal Characteristics





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

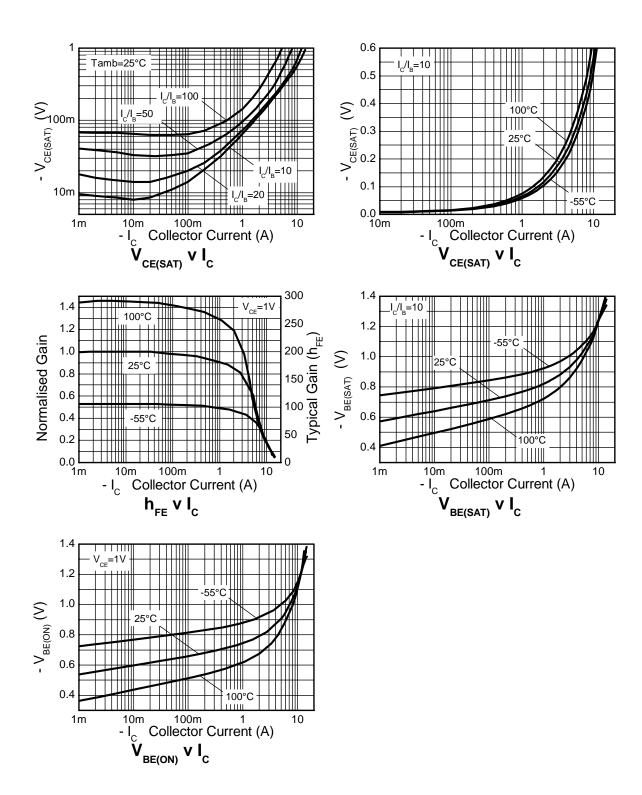
Characteristic	Symbol	Min	Тур.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-100	-125	_	V	$I_{C} = -100 \mu A$
Collector-Base Breakdown Voltage	BV _{CER}	-100	-125	_	V	$I_C = -100\mu A, R_{BE} \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-60	-80	_	V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.1	_	V	$I_E = -100 \mu A$
Collector Cutoff Current	I _{CBO}	1	<1	-20	nA	$V_{CB} = -80V$
Emitter Cutoff Current	I _{EBO}	-	<1	-10	nA	$V_{EB} = -6V$
Emitter Cutoff Current	I _{CER}	_	<1	-20	nA	V _{CE} = -80V, R _{BE} ≤1kΩ
DC Current Transfer Static Ratio (Note 11)	h _{FE}	100 100 50 15	230 200 110 40	300 — —	_	$\begin{split} I_C &= -10 \text{mA}, \ V_{CE} = -1 \text{V} \\ I_C &= -2 \text{A}, \ V_{CE} = -1 \text{V} \\ I_C &= -6 \text{A}, \ V_{CE} = -1 \text{V} \\ I_C &= -10 \text{A}, \ V_{CE} = -1 \text{V} \end{split}$
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(SAT)}	I	-13 -60 -115 -315	-25 -90 -165 -400	mV	$\begin{split} I_C &= \text{-0.1A}, \ I_B = \text{-10mA} \\ I_C &= \text{-1A}, \ I_B = \text{-100mA} \\ I_C &= \text{-2A}, \ I_B = \text{-200mA} \\ I_C &= \text{-6A}, \ I_B = \text{-600mA} \end{split}$
Base-Emitter Saturation Voltage (Note 11)	$V_{BE(SAT)}$		-1.05	-1.2	V	$I_C = -6A$, $I_B = -600mA$
Base-Emitter Turn-On Voltage (Note 11)	$V_{BE(ON)}$	1	-0.92	-1.05	V	$I_C = -6A, V_{CE} = -1V$
Transitional Frequency	f _T	_	120	_	MHz	$I_C = -100 \text{mA}, V_{CE} = -10 \text{V}$ f = 50MHz
Output Capacitance	C_{OBO}	_	74	_	pF	$V_{CB} = -10V$, $f = 1MHz$,
Switching Times	ton toff	_	82 350	_	ns	$I_C = -2A$, $V_{CC} = -10V$, $I_{B1} = I_{B2} = -200\text{mA}$

Note:

11. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤2%.



Typical Electrical Characteristics

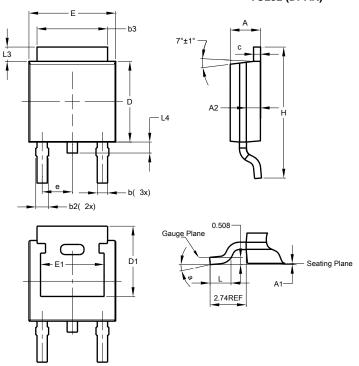




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

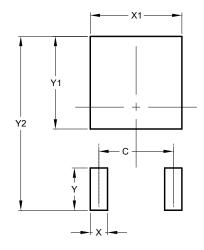


TO252 (DPAK)				
Dim	Min	Max	Тур	
Α	2.19	2.39	2.29	
A1	0.00	0.13	0.08	
A2	0.97	1.17	1.07	
b	0.64	0.88	0.783	
b2	0.76	1.14	0.95	
b3	5.21	5.46	5.33	
С	0.45	0.58	0.531	
D	6.00	6.20	6.10	
D1	5.21	_	-	
е	_	_	2.286	
Е	6.45	6.70	6.58	
E1	4.32	_	_	
Н	9.40	10.41	9.91	
L	1.40	1.78	1.59	
L3	0.88	1.27	1.08	
L4	0.64	1.02	0.83	
а	0°	10°	_	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Υ	2.600		
Y1	5.700		
Y2	10.700		



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